

IN THE CLAIMS

Claims 1-13 (Canceled).

14 (Previously Presented). A process comprising:
forming a recess having a bottom and a wall;
forming an electrically resistive film in the recess to form a heater; and
treating the film to have different electrical conductivity at the bottom and the wall; and
forming a phase change material over said wall.

15 (Previously Presented). The process according to claim 14, wherein treating includes implanting the film at a first angle and implanting the polysilicon film at a second angle different from the first angle.

16 (Previously Presented). The process according to claim 14, wherein treating further comprises doping the film to form discrete isolated regions.

17 (Previously Presented). The process according to claim 14, before treating, further comprising:
forming a temporary material in the recess; and
patterning the temporary material to expose the film.

18 (Previously Presented). The process according to claim 14, before treating, further comprising:
forming a temporary material in the recess;
patterning a mask over the temporary material; and
removing a portion of the temporary material to expose the film.

Claims 19-45 (Canceled).